50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

31 August 2023

**Product data sheet** 

# 1. General description

NPN/NPN Resistor-Equipped double Transistor (RET) in a medium power SOT1118 (DFN2020-6) leadless Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PIMC31PA PNP/PNP complement: PIMP31PA

#### 2. Features and benefits

- 500 mA output current capability
- Built-in resistors
- Simplifies circuit design
- · Reduces component count
- · Reduces pick and place costs

# 3. Applications

- · Digital applications
- Cost-saving alternative to BC817 series in digital applications
- · Control of IC inputs
- Switching loads

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	500	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[1]	0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		[1]	9	10	11	

[1] See section "Test information" for resistor calculation and test conditions.



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	6 5 4	
3	O2	output (collector) TR2		R1   R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1	1 2 3	<u>                                   </u>
7	O1	output (collector) TR1	Transparent top view	
8	O2	output (collector) TR2	DFN2020-6 (SOT1118)	GND1 I1 O2 aaa-019894

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
PIMN31PA	DFN2020-6	plastic, leadless thermal enhanced ultra thin small outline package; no leads; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1118		

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PIMN31PA	8J

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

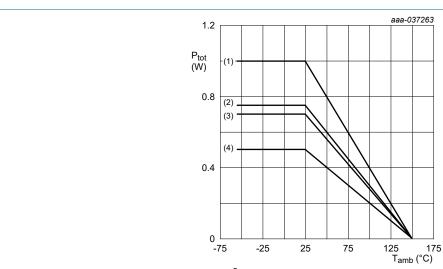
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or			'		
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
VI	input voltage			-5	10	V
Io	output current			-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	360	mW
			[2]	-	550	mW
			[3]	-	510	mW
			[4]	-	730	mW
Per device	<u> </u>		'	'		'
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	500	mW
			[2]	-	750	mW
			[3]	-	700	mW
			[4]	-	1	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35µm copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided, 35µm copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, 4-layer copper, standard footprint
- (4) FR4 PCB, single-sided, 35µm copper, standard footprint
- Fig. 1. Per device: Power derating curves for DFN2020-6 (SOT1118)

PIMN31PA

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	348	K/W
	junction to ambient		[2]	-	-	228	K/W
			[3]	-	-	246	K/W
			[4]	-	-	172	K/W
Per device	'		,	'		,	
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	250	K/W
- '	junction to ambient		[2]	-	-	167	K/W
			[3]	-	-	179	K/W
			[4]	-	-	125	K/W

- Device mounted on an FR4 PCB, single-sided, 35  $\mu m$  copper, tin-plated and standard footprint.
- [2] [3] Device mounted on an FR4 PCB, single-sided, 35μm copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.

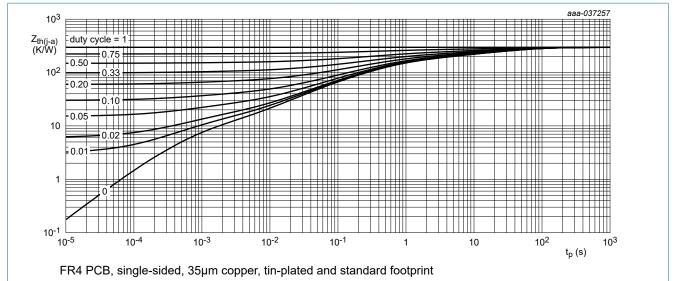
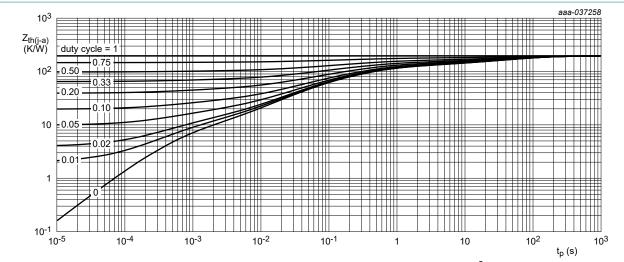


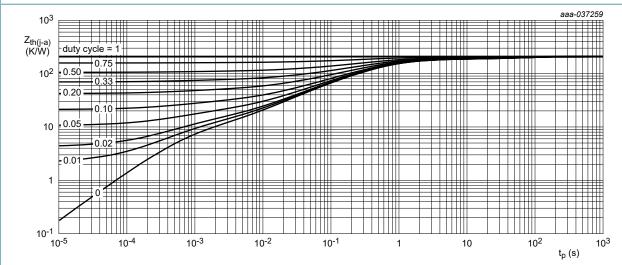
Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$



FR4 PCB, single-sided, 35µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

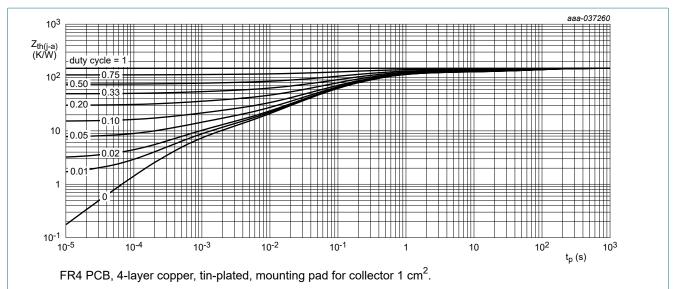


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

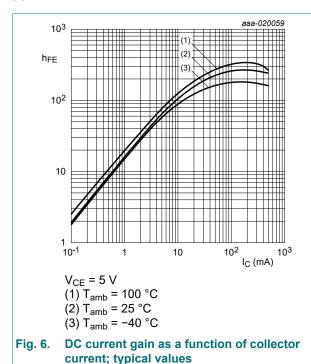
50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 50 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	0.5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	0.72	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C		70	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		0.3	0.6	1	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 20 mA; T <sub>amb</sub> = 25 °C		0.4	0.8	1.4	V
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[1]	0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		[1]	9	10	11	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	5	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	210	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.



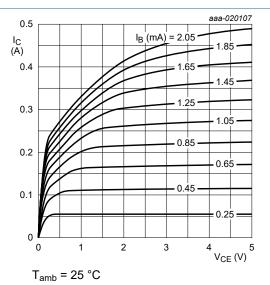
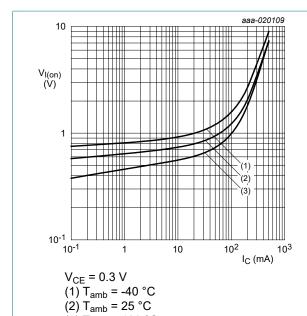
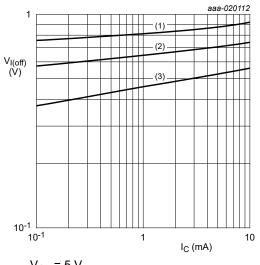


Fig. 7. Collector current as a function of collectoremitter voltage; typical values

### 50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

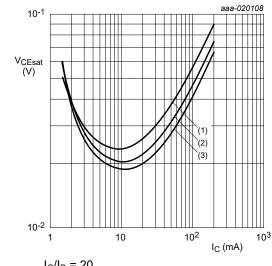


(3)  $T_{amb} = 100 \, ^{\circ}C$ Fig. 8. On-state input voltage as a function of collector | Fig. 9.



V<sub>CE</sub> = 5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

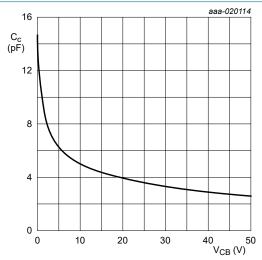




 $I_C/I_B = 20$ (1) T<sub>amb</sub> = 100 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

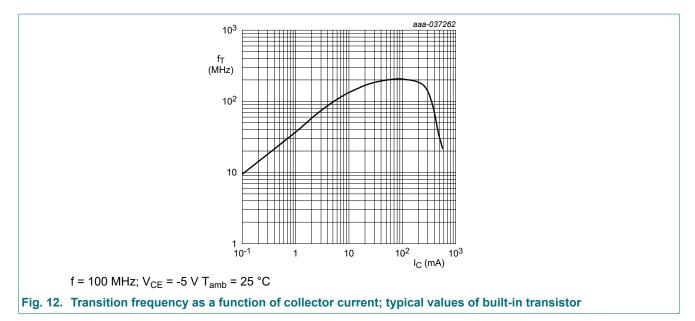
Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 11. Collector capacitance as a function of collectorbase voltage; typical values

### 50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$



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50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

# 11. Test information

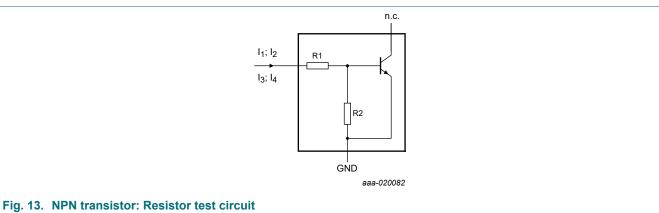
#### **Resistor calculation**

• Calculation of bias resistor 1 (R1):

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1):

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$



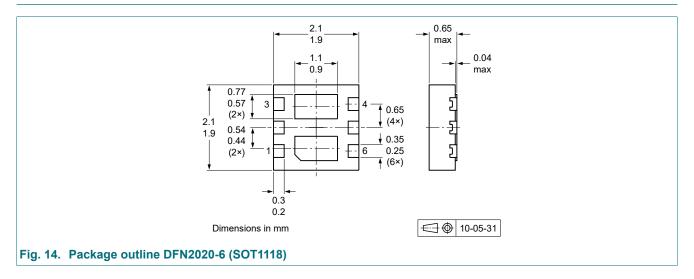
#### **Resistor test conditions**

**Table 8. Resistor test conditions** 

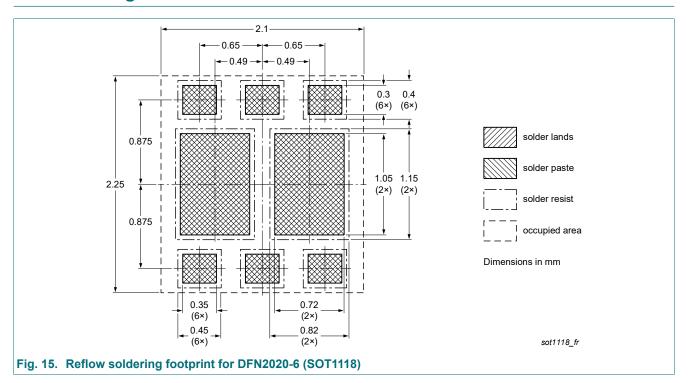
PIMN31PA	R1 (kΩ)	R2 (kΩ)	Test conditions	Test conditions				
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14		
TR1/TR2 (NPN)	1	10	0.7 mA	0.8 mA	-0.45 mA	-0.55 mA		

50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

# 12. Package outline



# 13. Soldering



50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMN31PA v.1	20230831	Product data sheet	-	-

#### 50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PIMN31PA

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### 50 V, 500 mA NPN/NPN Resistor-Equipped double Transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

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